

RF MOSFET Power Transistor, 40W, 28V

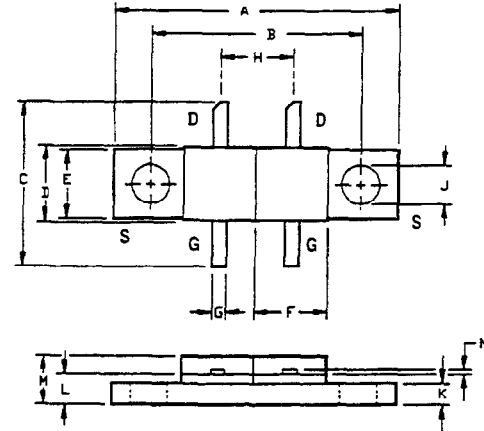
100 - 500 MHz

UF2840G

V2.00

Features

- N-Channel Enhancement Mode Device
- DMOS Structure
- Lower Capacitances for Broadband Operation
- High Saturated Output Power
- Lower Noise Figure Than Competitive Devices



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	20	V
Drain-Source Current	I_{DS}	4*	A
Power Dissipation	P_D	116	W
Junction Temperature	T_J	200	°C
Storage Temperature	T_{STG}	-55 to +150	°C
Thermal Resistance	θ_{JC}	1.52	°C/W

LETTER DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	24.64	24.89	.970	.980
B	18.29	18.54	.720	.730
C	13.72	14.22	.540	.560
D	6.22	6.48	.245	.255
E	5.72	5.97	.225	.235
F	6.22	6.48	.245	.255
G	1.14	1.40	.045	.055
H	6.22	6.48	.245	.255
J	3.18	3.43	.125	.135
K	1.78	2.03	.070	.080
L	2.34	2.84	.092	.112
M	3.99	4.75	.157	.187
N	.08	.15	.003	.006

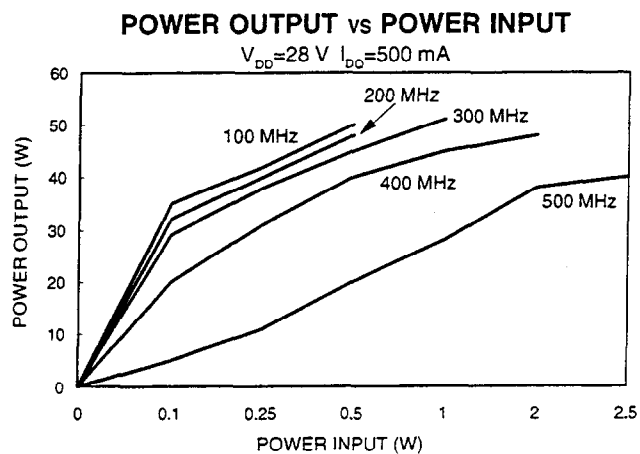
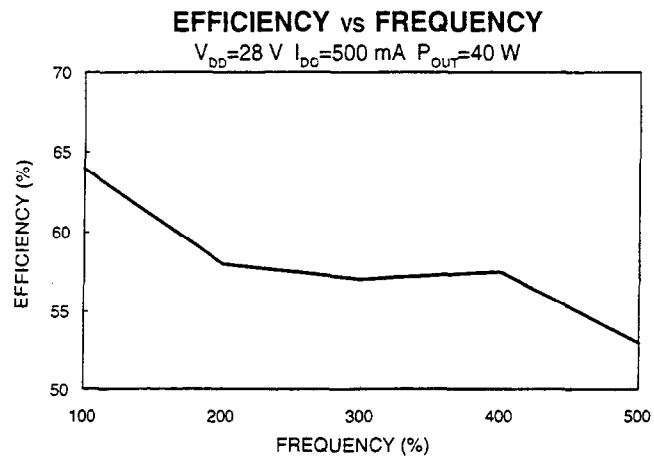
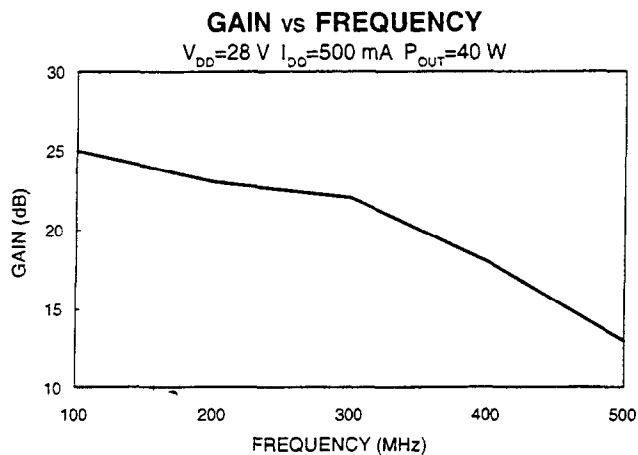
Electrical Characteristics at 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	65	-	V	$V_{GS}=0.0\text{ V}$, $I_{DS}=5.0\text{ mA}^*$
Drain-Source Leakage Current	I_{DSS}	-	1.0	mA	$V_{DS}=28.0\text{ V}$, $V_{GS}=0.0\text{ V}^*$
Gate-Source Leakage Current	I_{GSS}	-	1.0	μA	$V_{GS}=20\text{ V}$, $V_{DS}=0.0\text{ V}^*$
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	6.0	V	$V_{DS}=10.0\text{ V}$, $I_{DS}=100.0\text{ mA}^*$
Forward Transconductance	G_M	.500	-	S	$V_{DS}=10.0\text{ V}$, $I_{DS}=1.0\text{ A}$, $\Delta V_{GS}=1.0\text{ V}$, 80 μs Pulse*
Input Capacitance	C_{ISS}	-	45	pF	$V_{DS}=28.0\text{ V}$, $F=1.0\text{ MHz}^*$
Output Capacitance	C_{OSS}	-	30	pF	$V_{DS}=28.0\text{ V}$, $F=1.0\text{ MHz}^*$
Reverse Capacitance	C_{RSS}	-	8	pF	$V_{DS}=28.0\text{ V}$, $F=1.0\text{ MHz}^*$
Power Gain	G_P	10	-	dB	$V_{DS}=28.0\text{ V}$, $I_{DS}=500.0\text{ mA}$, $P_{OUT}=40.0\text{ W}$, $F=500\text{ MHz}$
Drain Efficiency	η_D	50	-	%	$V_{DS}=28.0\text{ V}$, $I_{DS}=500.0\text{ mA}$, $P_{OUT}=40.0\text{ W}$, $F=500\text{ MHz}$
Load Mismatch Tolerance	VSWR-T	-	30:1	-	$V_{DS}=28.0\text{ V}$, $I_{DS}=500.0\text{ mA}$, $P_{OUT}=40.0\text{ W}$, $F=500\text{ MHz}$

* Per Side

Specifications Subject to Change Without Notice.

Typical Broadband Performance Curves



Typical Device Impedance

Frequency (MHz)	Z_{IN} (OHMS)	Z_{LOAD} (OHMS)
100	$6.0 - j 20.0$	$25.0 + j 27.0$
200	$3.5 - j 11.5$	$16.5 + j 19.5$
300	$2.5 - j 5.5$	$13.0 + j 13.0$
400	$3.0 + j 0.0$	$12.0 + j 9.0$
500	$4.0 + j 3.0$	$12.0 + j 5.0$

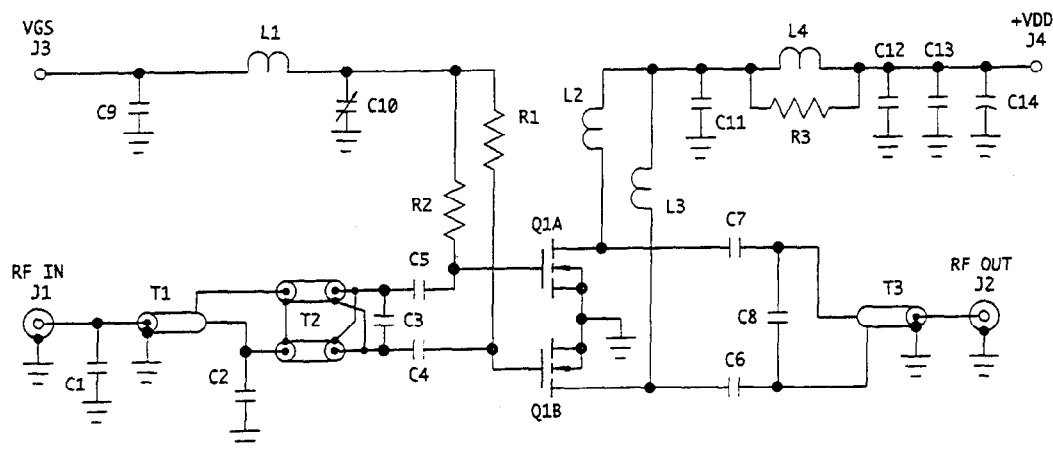
$$V_{DD}=28\text{ V}, I_{DQ}=500\text{ mA}, P_{OUT}=40.0\text{ Watts}$$

Z_{in} is the series equivalent input impedance of the device from gate to gate.

Z_{LOAD} is the optimum series equivalent load impedance as measured from drain to ground.

RF Test Fixture

VDS = 28 VOLTS
IDQ = 500mA



PARTS LIST

C1,C3	CAPACITOR 15pF
C2	CAPACITOR 7pF
C4,C5,C6,	CHIP CAPACITOR 620pF ATC
C7	
C8	CHIP CAPACITOR 9.1pF ATC
C9,C12	CAPACITOR 1000pF
C10	TRIMMER CAPACITOR 2-500pF
C11	CAPACITOR ATC 500pF
C13	MONOLITHIC CERAMIC CAPACITOR 0.1uF
C14	ELECTROLYTIC CAPACITOR 50uF 50 V.
L1	4 TURNS OF NO. 22 AWG ON '0.35"
L2,L3	6 TURNS OF NO. 22 AWG ON '0.35"
L4	8 TURNS OF NO. 22 AWG ON R3
R1,R2	RESISTOR 12K OHMS 0.25 WATT
R3	RESISTOR 33 OHMS 3 WATTS
T1	50 OHM SEMI-RIGID COAX 2.1" X '0.085"
T2	25 OHM SEMI-RIGID COAX 2X 2.3" X '0.070"
T3	25 OHM SEMI-RIGID COAX 3.3" X '0.070"
Q1	UF2840G
BOARD	FR4 0.062"